TOSHIBA Multichip Discrete Device

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HN7G03FU

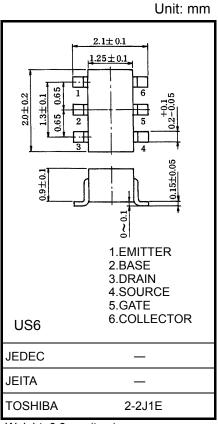
Power Management Switch Applications
Driver Circuit Applications
Interface Circuit Applications

Q1 (transistor) : 2SA1955 equivalent

Q2 (S-MOS) : SSM3K04FU equivalent

Q1 Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-15	V
Collector-emitter voltage	V _{CEO}	-12	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ic	-400	mA
Base current	ΙΒ	-50	mA



Weight: 6.8 mg (typ.)

Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V _{GSS}	10	V
Drain current	ΙD	100	mA

Q1, Q2 Common Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Power dissipation	P*	200	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	−55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

^{*} Total rating.

Q1 Electrical Characteristics (Ta = 25°C)

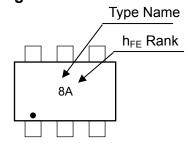
www.DataSheet4U.com Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current	I _{CBO}	_	V _{CB} =- 15 V, I _E = 0	_	_	-0.1	μΑ
Emitter cutoff current	I _{EBO}	_	V _{EB} =- 5 V, I _C = 0	_	_	-0.1	μΑ
DC current gain	h _{FE} (Note 1)	_	V _{CE} =- 2 V, I _C =- 10 mA	300	_	1000	
Collector-emitter saturation voltage	V _{CE(sat) (1)}	_	I _C =- 10 mA, I _B =- 0.5 mA	_	-15	-30	mV
	V _{CE(sat) (2)}	_	I _C =- 200 mA, I _B =- 10 mA	_	-110	-250	IIIV
Base-emitter saturation voltage	V _{BE(sat)}	_	I _C =- 200 mA, I _B =- 10 mA	ı	-0.87	-1.2	V

Note 1: hFE classification A: 300~600, B: 500~1000

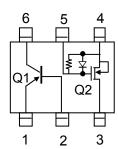
Q2 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	_	V _{GS} = 10 V, V _{DS} = 0	_	_	15	μΑ
Drain-source breakdown voltage	V _{(BR) DSS}	_	I _D = 100 μA, V _{GS} = 0	20	_	_	V
Drain current	I _{DSS}	_	V _{DS} = 20 V, V _{GS} = 0		_	1	μA
Gate threshold voltage	V _{th}	_	V _{DS} = 3 V, I _D = 0.1 mA	0.7	_	1.3	V
Forward transfer admittance	Y _{fs}	_	V _{DS} = 3 V, I _D = 10 mA	25	50	1	mS
Drain-source ON-resistance	R _{DS(ON)}	_	I _D = 10 mA, V _{GS} = 2.5 V	_	4	12	Ω
Gate-source ON-resistance	R _{GS}	_	V _{GS} = 0 ~ 10 V	0.7	1.0	1.3	МΩ

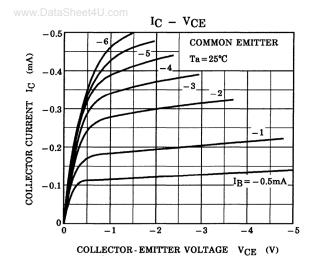
Marking

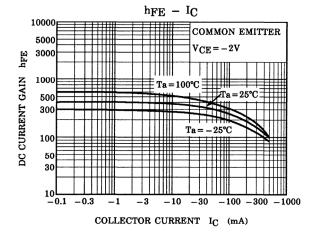


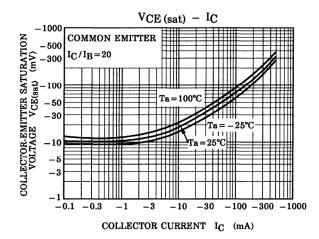
Equivalent Circuit (Top View)

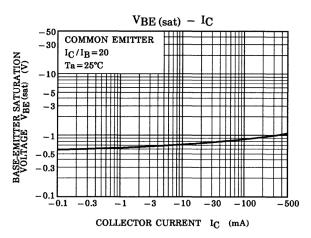


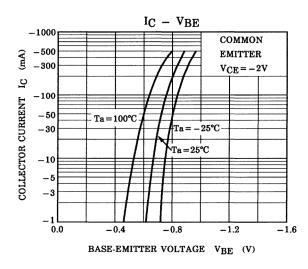
Q1

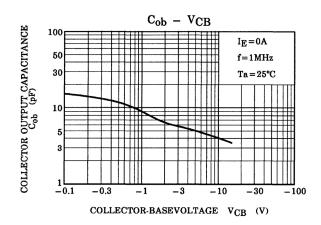






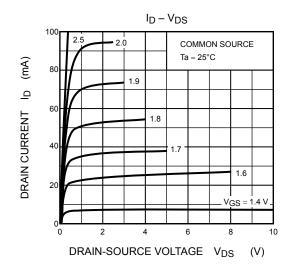


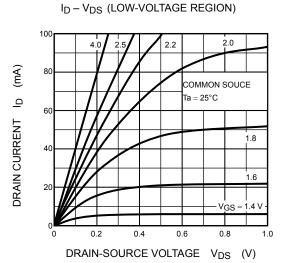


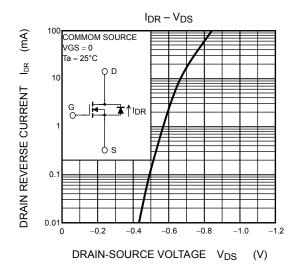


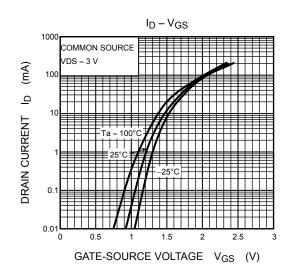
Q2

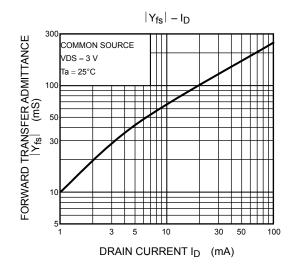
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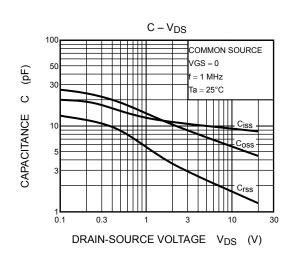






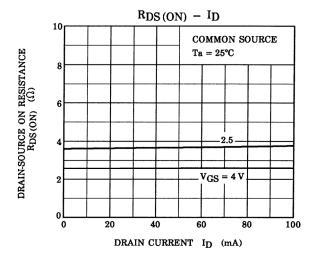


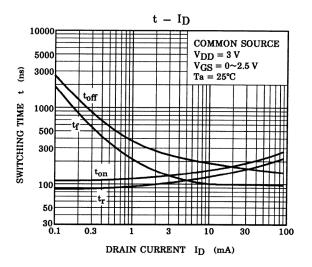


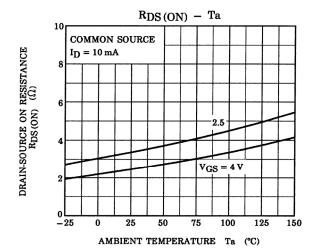


Q2

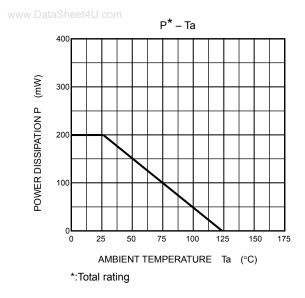
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Q1, Q2 common



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